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BYV255V

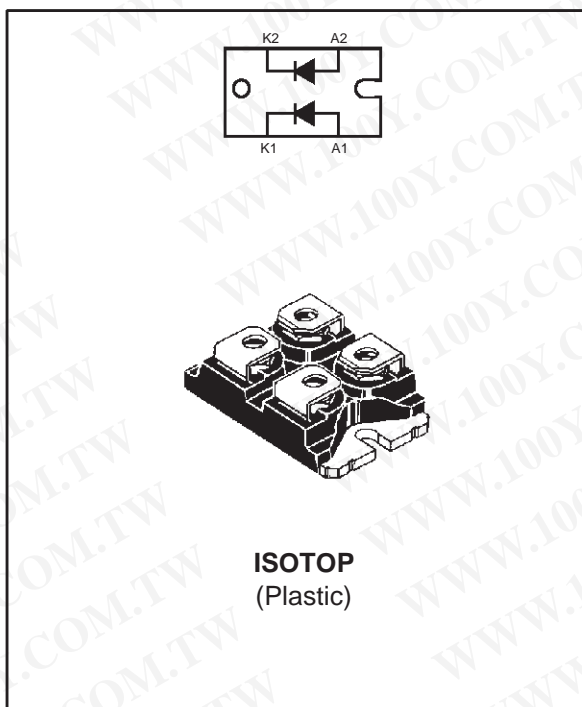
HIGH EFFICIENCY FAST RECOVERY RECTIFIER DIODES

FEATURES

- SUITED FOR SMPS
- VERY LOW FORWARD LOSSES
- NEGLIGIBLE SWITCHING LOSSES
- HIGH SURGE CURRENT CAPABILITY
- HIGH AVALANCHE ENERGY CAPABILITY
- INSULATED :
Insulating voltage = 2500 V_{RMS}
Capacitance = 55 pF

DESCRIPTION

Dual rectifier suited for switchmode power supply and high frequency DC to DC converters. Packaged in ISOTOP™ this device is intended for use in low voltage, high frequency inverters, free wheeling and polarity protection applications.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
I _{F(RMS)}	RMS forward current		Per diode 150	A
I _{F(AV)}	Average forward current $\delta = 0.5$	T _c =110°C	Per diode 100	A
I _{FSM}	Surge non repetitive forward current	t _p =10ms sinusoidal	Per diode 1600	A
T _{stg} T _j	Storage and junction temperature range		- 40 to + 150 - 40 to + 150	°C °C

Symbol	Parameter	Value	Unit
V _{RRM}	Repetitive peak reverse voltage	200	V

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THERMAL RESISTANCE

Symbol	Parameter	Value	Unit	
Rth (j-c)	Junction to case	Per diode	0.4	°C/W
		Total	0.25	
Rth (c)	Coupling	0.1	°C/W	

When the diodes 1 and 2 are used simultaneously :

$$T_j - T_c (\text{diode 1}) = P(\text{diode 1}) \times R_{th(j-c)} (\text{Per diode}) + P(\text{diode 2}) \times R_{th(c)}$$

ELECTRICAL CHARACTERISTICS (Per diode) STATIC CHARACTERISTICS

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
I _R *	T _j = 25°C	V _R = V _{R_{RM}}			100	μA
	T _j = 100°C				10	mA
V _F **	T _j = 125°C	I _F = 100 A			0.85	V
	T _j = 125°C	I _F = 200 A			1.00	
	T _j = 25°C	I _F = 200 A			1.15	

Pulse test : * t_p = 5 ms, duty cycle < 2 %

** t_p = 380 μs, duty cycle < 2 %

RECOVERY CHARACTERISTICS

Symbol	Test Conditions			Min.	Typ.	Max.	Unit
trr	T _j = 25°C	I _F = 0.5A I _R = 1A	I _{rr} = 0.25A			55	ns
		I _F = 1A V _R = 30V	dI _F /dt = -50A/μs			80	
tfr	T _j = 25°C	I _F = 1A V _{FR} = 1.1 x V _F	tr = 5 ns		10		ns
V _{FP}	T _j = 25°C	I _F = 1A	tr = 5 ns		1.5		V

TURN-OFF SWITCHING CHARACTERISTICS

Symbol	Test Conditions			Min.	Typ.	Max.	Unit
I _{RM}	T _j = 100°C	I _F = 100A L _p @ 0.05μH V _{CC} @ 0.6 V _{R_{RM}}	dI _F /dt = -200A/μs			16	A
			dI _F /dt = -400A/μs		24		

Fig.1 : Average forward power dissipation versus average forward current.

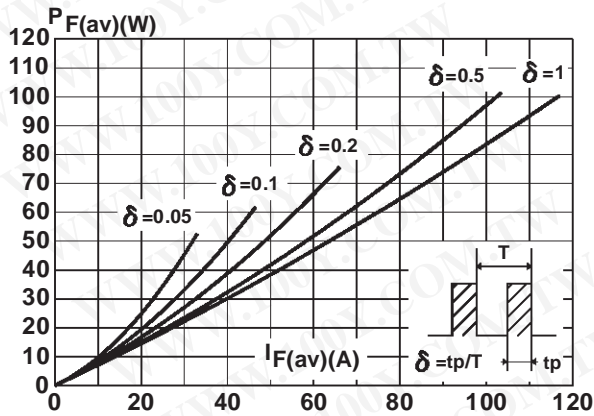


Fig.2 : Peak current versus form factor.

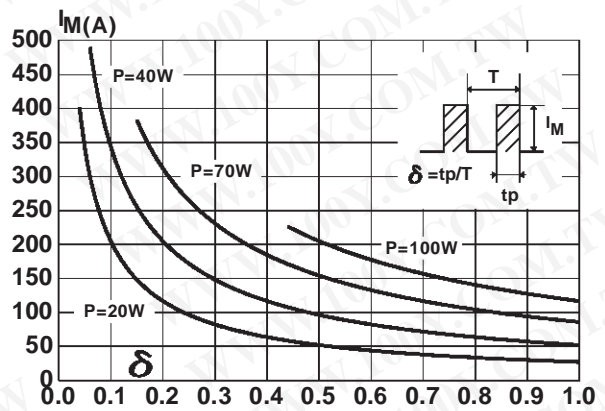


Fig.3 : Forward voltage drop versus forward current (maximum values).

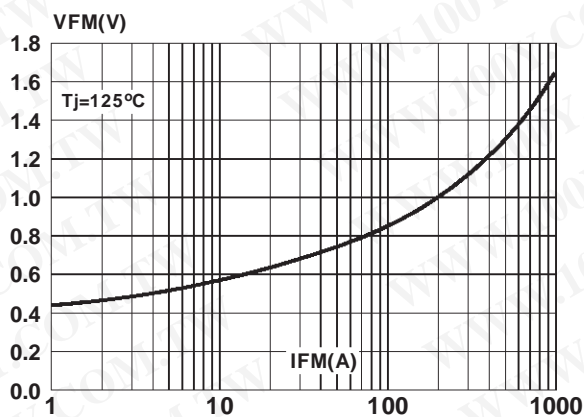


Fig.4 : Relative variation of thermal impedance junction to case versus pulse duration.

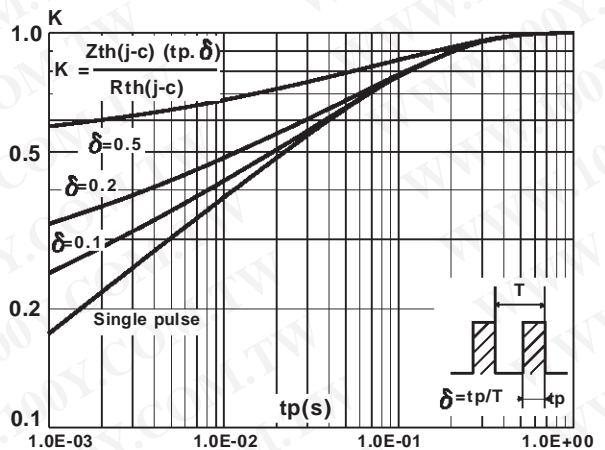


Fig.5 : Non repetitive surge peak forward current versus overload duration.

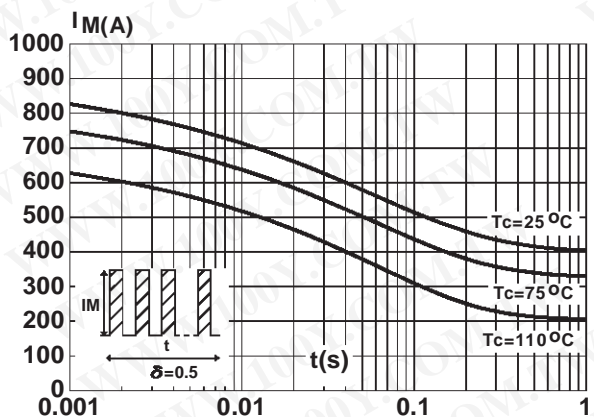
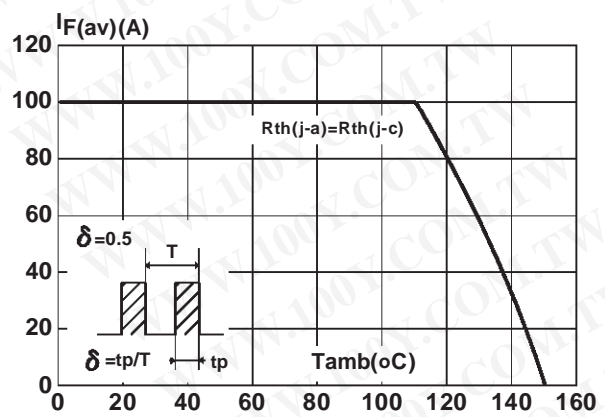


Fig.6 : Average current versus ambient temperature. (duty cycle : 0.5)



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Fig.7 : Junction capacitance versus reverse voltage applied (Typical values).

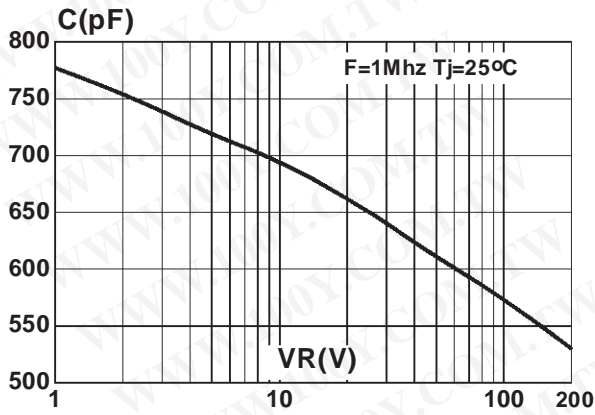


Fig.8 : Recovery charges versus dI_F/dt .

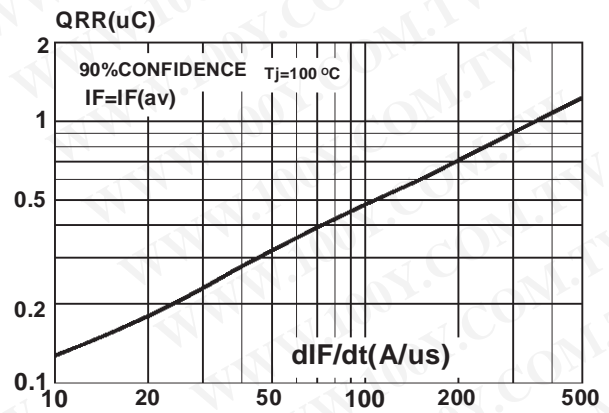


Fig.9 : Peak reverse current versus dI_F/dt .

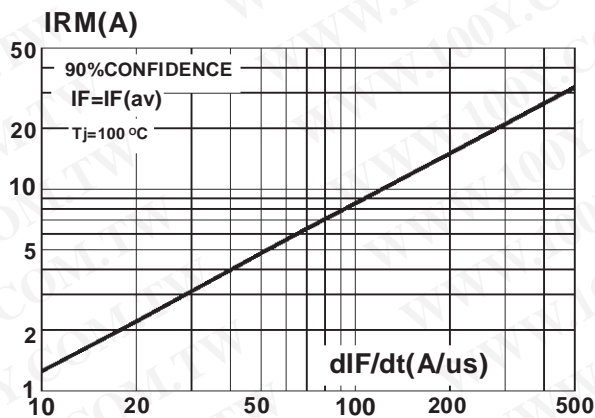
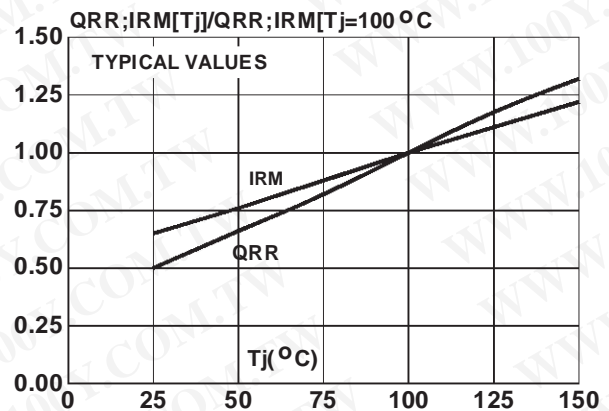
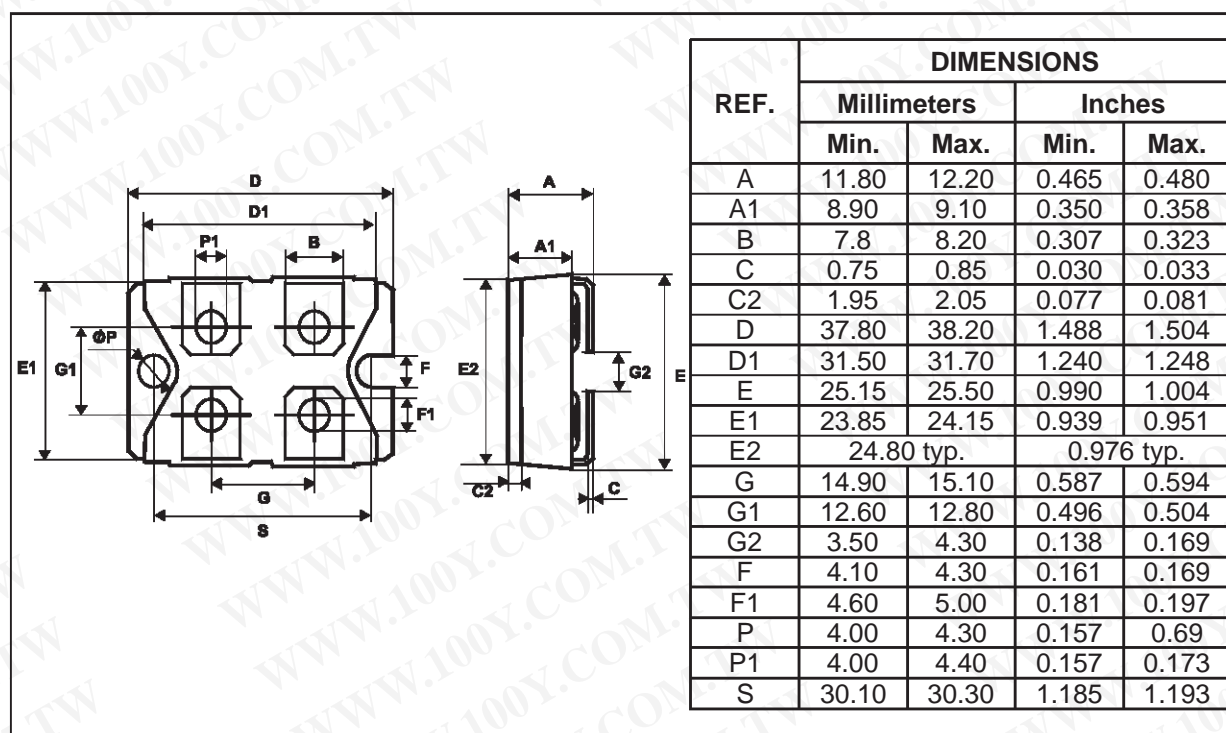


Fig.10 : Dynamic parameters versus junction temperature.



PACKAGE MECHANICAL DATA
 ISOTOP


- **Marking** : Type number
- Cooling method : C
- Weight : 27 g
- Epoxy meets UL94, V0

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